

IN THE CLAIMS:

Claims 1 to 10 (cancelled)

Claim 11 (currently amended) A method of fabricating an organic thin-film transistor comprising a substrate and an organic semiconductor layer, wherein the organic semiconductor layer is obtained by controlling temperature of the substrate to 30°C or higher and 65°C or lower and vacuum-depositing tetradecafluoropentacene ($C_{22}F_{14}$) on the substrate at 1×10^{-4} pascals or lower.

Claim 12 (currently amended) A method of fabricating an organic thin-film transistor comprising a substrate and an organic semiconductor layer, wherein the organic semiconductor layer is obtained by controlling temperature of the substrate to 24°C or higher and 60°C or lower and vacuum-depositing dodecafluoronaphthacene ($C_{18}F_{12}$) on the substrate at 1×10^{-4} pascals or lower.

Claim 13 (currently amended) An organic thin-film transistor comprising a substrate and thin films of gate electrode, gate insulating film, an organic semiconductor layer containing a fluorinated acene compound, and source and drain electrodes stacked on the substrate in order, wherein the thin film of organic semiconductor layer is obtained by controlling temperature of the substrate and vacuum-depositing on the surface a fluorinated acene compound which is represented by a formula of $C_{4n+2}F_{2n+4}$, wherein n is an integer of 2 or greater.

Claims 14, 15, and 16 (cancelled)